Preferred Devices

Thyristor Surge Protectors

High Voltage Bidirectional TSPD

These Thyristor Surge Protective devices (TSPD) prevent overvoltage damage to sensitive circuits by lightning, induction and power line crossings. They are breakover—triggered crowbar protectors. Turn—off occurs when the surge current falls below the holding current value.

- High Surge Current Capability: 80 Amps 10 x 1000 μsec, for Controlled Temperature Environments
- The MMT08B310 is used to help equipment meet various regulatory requirements including: Bellcore 1089, ITU K.20 & K.21, IEC 950, UL 1459 & 1950 and FCC Part 68.
- Bidirectional Protection in a Single Device
- Little Change of Voltage Limit with Transient Amplitude or Rate
- Freedom from Wearout Mechanisms Present in Non–Semiconductor Devices
- Fail-Safe, Shorts When Overstressed, Preventing Continued Unprotected Operation
- Surface Mount Technology (SMT)
- N Indicates UL Registered File #E210057

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Off-State Voltage - Maximum MMT08B310T3	V _{DM}	±270	V
Maximum Pulse Surge Short Circuit Current Non-Repetitive Double Exponential Decay Waveform (Notes 1 and 2) 10 x 1000 μsec (-25°C Initial Temperature) 8 x 20 μsec 10 x 160 μsec 10 x 560 μsec	I _{PPS1} I _{PPS2} I _{PPS3} I _{PPS4}	±80 ±250 ±150 ±100	A(pk)
Maximum Non–Repetitive Rate of Change of On–State Current Double Exponential Waveform, R = 1.0, L = 1.5 μ H, C = 1.67 μ F, I_{pk} = 110A	di/dt	±100	A/μs

- 1. Allow cooling before testing second polarity.
- 2. Measured under pulse conditions to reduce heating.



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BIDIRECTIONAL TSPD (%) 80 AMP SURGE 310 VOLTS





SMB (No Polarity) (Essentially JEDEC DO-214AA) CASE 403C

MARKING DIAGRAM



RPCJ = Specific Device Code

Y = Year WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping†
MMT08B310T3	SMB	12mm Tape and Reel (2.5K/Reel)

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Operating Temperature Range Blocking or Conducting State	T _{J1}	-40 to +125	°C
Overload Junction Temperature – Maximum Conducting State Only	T _{J2}	+175	°C
Instantaneous Peak Power Dissipation (I _{pk} = 50 A, 10x1000 μsec @ 25°C)	P _{PK}	2000	W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	TL	260	°C

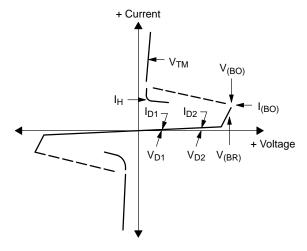
ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}\text{C}$ unless otherwise noted) Devices are bidirectional. All electrical parameters apply to forward and reverse polarities.

Characteristics		Symbol	Min	Тур	Max	Unit
Breakover Voltage (Both polarities) (dv/dt = 100 V/µs, I _{SC} = 1.0 A, Vdc = 1000 V) (+65°C)	MMT08B310T3	V _(BO)	_	-	365	V
(1.00 0)	MMT08B310T3		-	_	400	
Breakover Voltage (Both polarities)		V _(BO)				V
(f = 60 Hz, I_{SC} = 1.0 A(rms), V_{OC} = 1000 V(rms), R_I = 1.0 kΩ, t = 0.5 cycle) (Note 3) (+65°C)	MMT08B310T3		_	-	365	
(1.00 0)	MMT08B310T3		_	_	400	
Breakover Voltage Temperature Coefficient		dV _(BO) /dT _J	-	0.08	-	%/°C
Breakdown Voltage (I _(BR) = 1.0 mA) Both polarities	MMT08B310T3	V _(BR)	_	310	-	V
Off State Current ($V_{D1} = 50 \text{ V}$) Both polarities ($V_{D2} = V_{DM}$) Both polarities		I _{D1} I _{D2}	_ _		2.0 5.0	μΑ
On–State Voltage (I_T = 1.0 A) (PW \leq 300 μ s, Duty Cycle \leq 2%) (Note 3)		V _T	_	1.53	3.0	V
Breakover Current (f = 60 Hz, V _{DM} = 1000 V(rms), R _S = Both polarities	= 1.0 kΩ)	I _{BO}	_	230	-	mA
Holding Current (Both polarities) $V_S = 500 \text{ Volts}$; I_T (Initiating Current) = $\pm 1.0 \text{ Amp}$	(Note 3)	I _H	150	340	-	mA
Critical Rate of Rise of Off–State Voltage (Linear waveform, V_D = Rated V_{BR} , T_J = 25°C)		dv/dt	2000	_	_	V/µs
Capacitance (f = 1.0 MHz, 50 Vdc, 1.0 V rms Signal) (f = 1.0 MHz, 2.0 Vdc, 1.0 mV rms Signal)		Co	_ _	23 45	- 50	pF

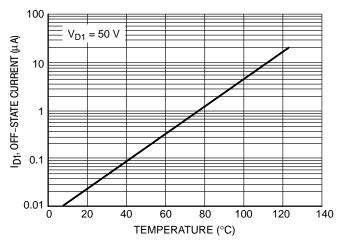
^{3.} Measured under pulse conditions to reduce heating.

Voltage Current Characteristic of TSPD (Bidirectional Device)

Symbol	Parameter
I _{D1} , I _{D2}	Off State Leakage Current
V _{D1} , V _{D2}	Off State Blocking Voltage
V _{BR}	Breakdown Voltage
V _{BO}	Breakover Voltage
I _{BO}	Breakover Current
I _H	Holding Current
V_{TM}	On State Voltage



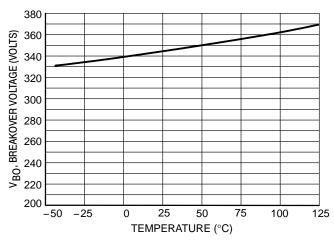
340



V_{BR}, BREAKDOWN VOLTAGE (VOLTS) 320 300 280 260 240 220 200 180 160 -25 25 50 75 100 125 -50 TEMPERATURE (°C)

Figure 1. Off-State Current versus Temperature

Figure 2. Breakdown Voltage versus Temperature



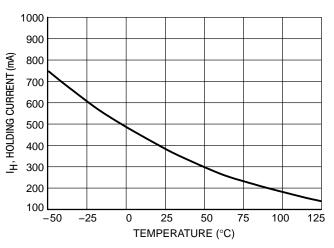
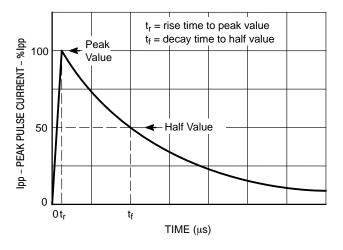


Figure 3. Breakover Voltage versus Temperature

Figure 4. Holding Current versus Temperature



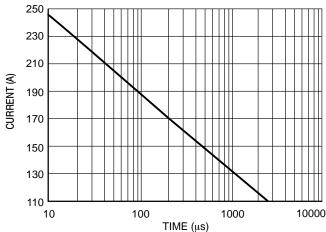
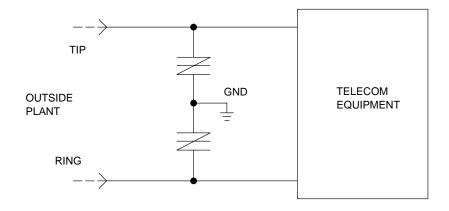
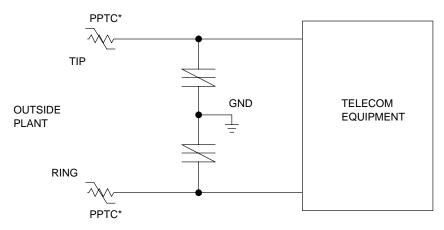


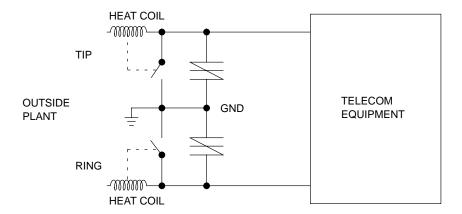
Figure 5. Exponential Decay Pulse Waveform

Figure 6. Peak Surge On-State Current versus Surge Current Duration, Sinusoidal Waveform





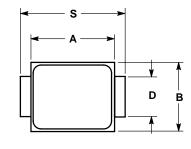
*Polymeric PTC (positive temperature coefficient) overcurrent protection device

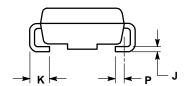


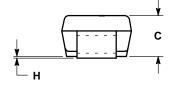
PACKAGE DIMENSIONS

SMB

(No Polarity) (Essentially JEDEC DO–214AA) CASE 403C-01 ISSUE A







- NOTES:

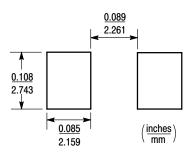
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: INCH.

 3. D DIMENSION SHALL BE MEASURED WITHIN DIMENSION P.

	INCHES		INCHES MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.160	0.180	4.06	4.57
В	0.130	0.150	3.30	3.81
С	0.075	0.095	1.90	2.41
D	0.077	0.083	1.96	2.11
Н	0.0020	0.0060	0.051	0.152
J	0.006	0.012	0.15	0.30
K	0.030	0.050	0.76	1.27
Р	0.020 REF		0.020 REF 0.51 REF	
S	0.205	0.220	5.21	5.59

SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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